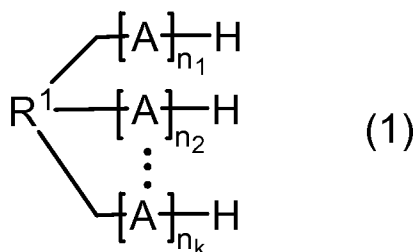


Amendments to the Claims

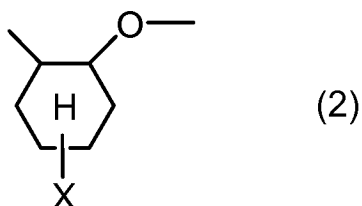
This is a complete listing of claims and supersedes all other listings:

1. Cancelled
2. Cancelled
3. Cancelled
4. Cancelled
5. Cancelled

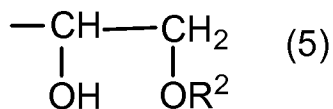
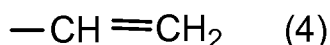
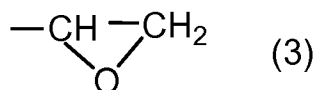
6. (Currently amended) A method for forming a pattern, characterized in that the method comprises: a first step of applying to a substrate a radiation-sensitive negative-type resist composition for pattern formation ~~as recited in claim 1;~~ and the radiation-sensitive negative-type resist composition for pattern formation contains an epoxy resin, a radiation-sensitive cationic polymerization initiator, and a solvent for dissolving the epoxy resin therein, characterized in that the resist composition, through drying, forms a resist film having a softening point falling within a range of 30 to 120°C and that the epoxy resin is represented by formula (1):



wherein R₁ represents a moiety derived from an organic compound having k active hydrogen atoms (k represents an integer of 1 to 100); each of n₁, n₂, through n_k represents 0 or an integer of 1 to 100; the sum of n₁, n₂, through n_k falls within a range of 1 to 100; and each of “A”s, which may be identical to or different from each other, represents an oxycyclohexane skeleton represented by formula (2):



wherein X represents any of groups represented by formulas (3) to (5):



(wherein R² represents a hydrogen atom, an alkyl group, or an acyl group), and at least two groups represented by formula (3) are contained in one molecule of the epoxy resin)); a second step of drying the substrate coated with the radiation-sensitive negative-type resist composition for pattern formation, to thereby form a resist film which has a thickness of at least 50 μ m; a third step of selectively exposing the formed resist film to an active energy beam according to a desired pattern; a fourth step of heating the exposed resist film so as to enhance a contrast of a pattern to be formed; and a fifth step of developing the heated resist film, to thereby remove the unexposed area of the resist film through dissolution, thereby forming a patterned layer.

7. Cancelled.

8. (Original) A method for forming a pattern according to claim 6, wherein the method includes, after completion of the fifth step, a sixth step of applying to the patterned layer

a material other than that of the patterned layer such that spaces present in the patterned layer are filled, at least to some height, with the material, to thereby form a second layer.

9. (Original) A method for forming a pattern according to claim 8, wherein the second layer is formed through metal plating.

10. (Original) A method for forming a pattern according to claim 8, wherein the second layer is formed by casting a photo-curable or heat-curable resin and curing the resin by light or heat.